REMARKS

Supplementing the Response filed August 20, 2004, wherein Applicants elected the Group II claims, Applicants are amending the Group II claims in order to further clarify the definition of aspects of the present invention defined therein. Specifically, claim 1 has been amended to recite that the deposited film, of the first gate insulating film, is formed over the thermally oxidized film and has a thickness greater than that of the thermally oxidized film; to recite that the element isolation region is formed by forming grooves in the substrate, depositing an insulating film over the grooves by a vapor deposition method and by polishing the insulating film so as to bury the insulating film in the grooves.

Independent claim 5 has been amended to recite that the first gate insulating film includes a thermally oxidized film and a deposited film formed over the thermally oxidized film and having a thickness greater than that of the thermally oxidized film; to recite that the second gate insulating film includes a thermally oxidized film; and to recite that an insulating region having a thickness greater than that of the first gate insulating film is formed by forming grooves in the substrate, depositing an insulating film over the grooves by a vapor deposition method and polishing the insulating film so as to bury the insulating film in the grooves.

Independent claim 13 has been amended to recite that the first gate insulating film includes a thermally oxidized film and a deposited film formed over the thermally oxidized film and having a thickness greater than that of the thermally oxidized film; to recite that the second gate insulating film includes a thermally oxidized film; and to recite an insulating region as discussed previously in connection with claim 5,

claim 13 being further amended to recite that the insulating film (of the insulating region) is integrally formed with an element isolation film defining a first MISFET forming region, and to recite that an etching rate of the insulating film buried in the groove is lower than that of the thermally oxidized film.

Independent claim 19 has been amended to recite that the first gate insulating film includes a thermally oxidized film and a deposited film formed over the thermally oxidized film, with the second gate insulating film including a thermally oxidized film and a deposited film formed over the thermally oxidized film and having a thickness thinner than that of the deposited film of the first insulating film; and to recite formation of an insulating region as discussed previously in connection with claim 5.

Moreover, claims 2 and 6 have been amended to recite relative etching rates of the insulating film buried in the groove and of the thermally oxidized film. Various of the claims previously in the application have been cancelled without prejudice or disclaimer, and others of the claims previously in the application have been amended, including dependency thereof, in light of canceling of claims previously in the application and amendments to the independent claims.

In connection with the present amendments, note pages 9-11, together with Embodiment 1 on pages 16-35, of Applicants' specification.

The restriction requirement and the election-of-species requirement, each set forth in the Office Action mailed July 20, 2004, are noted. The claims, of claims 1-26, remaining in the application after present amendments, remain as claims directed to the elected semiconductor device. In addition, it is respectfully submitted that the remaining claims, of claims 1-26 (that is, claims 1-7, 9, 10, 13, 15, 16, 19, 20, 22, 23, 25 and 26) all read on the elected species of the first embodiment, of

Fig. 1.

Entry of the present amendments; and, subsequent thereto, examination of the above-identified application in due course, are respectfully requested.

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Respectfully submitted,

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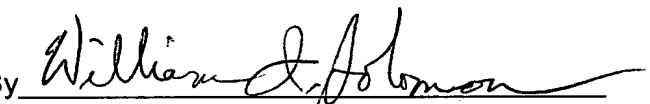
By 

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